



## 60V Dual N-Channel Enhancement Mode MOSFET

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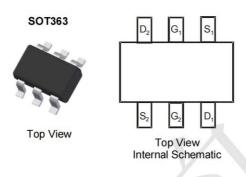
#### **Features**

- Fast switching
- Green Device Available
- Suit for 1.5V Gate Drive Applications

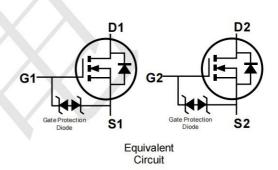
### **Application**

- Notebook
- Load Switch
- Networking
- Hand-held Instruments

## Package and Pin Configuration



#### Circuit diagram



# Marking: TF ←

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		Vgs	±20	V	
Continuous Proin Current /T =150°C)	T <sub>A</sub> =25℃	- I <sub>D</sub>	0.3	Α	
Continuous Drain Current (T <sub>J</sub> =150°C)	T <sub>A</sub> =100℃		0.19		
Drain Current-Pulsed (Note 1)		I <sub>DM</sub>	0.8	Α	
Maximum Power Dissipation		P <sub>D</sub>	0.35	W	
Operating Junction and Storage Temperature Range		$T_{J}, T_{STG}$	-55 To 150	°C	

#### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	350	°C/W



# NTJD5121NT1G

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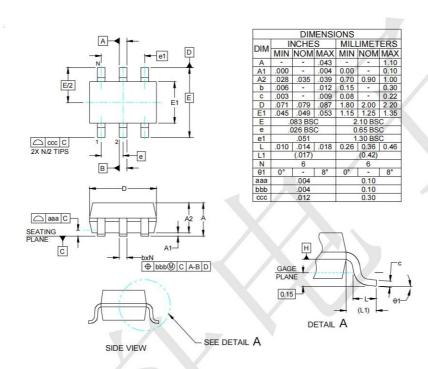
## Electrical Characteristics ( T<sub>A</sub> = 25°C unless otherwise noted )

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics					•	•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60		1-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =60 $V$ , $V_{GS}$ =0 $V$	-	-	1	μA
Cata Bada Laskana Cumant	L	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±1	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-		±10	uA
On Characteristics (Note 3)					•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.6	2.5	V
Desir Course On Chata Desiratores	D	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.2A	7 -	1.9	2.5	Ω
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.3A	-	1.8	2.2	Ω
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =0.2A	0.1	-	-	S
Dynamic Characteristics (Note4)			**			•
Input Capacitance	C <sub>lss</sub>	// =20/// =0//		27		PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz		18		PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F-1.UNITZ		2		PF
Switching Characteristics (Note 4)			•	•	•	
Turn-on Delay Time	t <sub>d(on)</sub>		_	10	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_{D}$ =0.2 $A$	_	50	1,14	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	V <sub>GS</sub> =10V,R <sub>GEN</sub> =10Ω -		17	18	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	11-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =10V,I <sub>D</sub> =0.3A, V <sub>GS</sub> =4.5V	-	1.7	3	nC
Drain-Source Diode Characteristics	7		*			7.5
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =0.2A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	0.3	Α

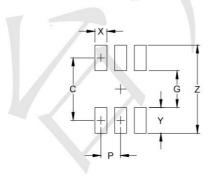


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## Outline Drawing - SOT-363(2.0X2.1)



## **Land Pattern - SOT-363**



DIMENSIONS			
DIM	<b>INCHES</b>	MILLIMETERS	
С	(.073)	(1.85)	
G	.039	1.00	
Р	.026	0.65	
X	.016	0.40	
Y	.033	0.85	
Z	.106	2.70	